



AO4601

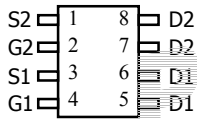
Complementary Enhancement Mode Field Effect Transistor

General Description

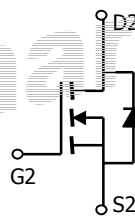
The AO4601 uses advanced trench technology MOSFETs to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

Features

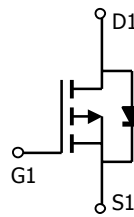
n-channel	p-channel
$V_{DS} (V) = 30V$	-30V
$I_D = 4.7A$	-8A
$R_{DS(ON)}$	$R_{DS(ON)}$
$< 55m\Omega (V_{GS}=10V)$	$< 18m\Omega (V_{GS} = 20V)$
$< 70m\Omega (V_{GS}=4.5V)$	$< 19m\Omega (V_{GS} = 10V)$
$< 110m\Omega (V_{GS} = 2.5V)$	



SOIC-8



n-channel



p-channel

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 12	± 25	V
Continuous Drain Current ^A	I_D	$T_A=25^\circ C$	4.7	-8
		$T_A=70^\circ C$	4	-6.9
Pulsed Drain Current ^B	I_{DM}	30	-50	A
Power Dissipation	P_D	$T_A=25^\circ C$	2	2
		$T_A=70^\circ C$	1.44	1.44
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Device	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	n-ch		62.5	$^\circ C/W$
Maximum Junction-to-Ambient ^A		n-ch		110	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	n-ch		50	$^\circ C/W$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	p-ch		62.5	$^\circ C/W$
Maximum Junction-to-Ambient ^A		p-ch		110	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	p-ch		35	$^\circ C/W$

n-channel MOSFET Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1	μA	
					5		
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			100	nA	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.6	1	1.4	V	
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	10			A	
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=4\text{A}$ $T_J=125^\circ\text{C}$		45	55	$\text{m}\Omega$	
			$V_{GS}=4.5\text{V}$, $I_D=3\text{A}$		55		70
			$V_{GS}=2.5\text{V}$, $I_D=2\text{A}$		83		110
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=4\text{A}$		8		S	
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.8	1	V	
I_S	Maximum Body-Diode Continuous Current				2.5	A	
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		390		pF	
C_{oss}	Output Capacitance			54.5		pF	
C_{rss}	Reverse Transfer Capacitance			41		pF	
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		3		Ω	
SWITCHING PARAMETERS							
Q_g	Total Gate Charge	$V_{GS}=4.5\text{V}$, $V_{DS}=15\text{V}$, $I_D=4\text{A}$		0.6		nC	
Q_{gs}	Gate Source Charge			1.38		nC	
Q_{gd}	Gate Drain Charge			4.34		nC	
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=3.75\Omega$, $R_{GEN}=6\Omega$		3.3		ns	
t_r	Turn-On Rise Time			1		ns	
$t_{D(off)}$	Turn-Off Delay Time			21.7		ns	
t_f	Turn-Off Fall Time			2.1		ns	
t_{rr}	Body Diode Reverse Recovery Time	$I_F=4\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		12		ns	
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=4\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		6.3		nC	

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

p-channel MOSFET Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 25\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1.7	-2.5	-3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$, $V_{DS}=-5\text{V}$	60			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-8\text{A}$ $T_J=125^\circ\text{C}$		15	19	$\text{m}\Omega$
		$V_{GS}=-20\text{V}$, $I_D=-8\text{A}$		14	18	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$, $I_D=-8\text{A}$		28		$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-8\text{A}$				S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		-0.75	-1	V
I_S	Maximum Body-Diode Continuous Current				-2.6	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-15\text{V}$, $f=1\text{MHz}$		2076		pF
C_{oss}	Output Capacitance			503		pF
C_{rss}	Reverse Transfer Capacitance			302		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		2		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $I_D=-12\text{A}$		37.2		nC
Q_{gs}	Gate Source Charge			7		nC
Q_{gd}	Gate Drain Charge			10.4		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $R_L=1.25\Omega$, $R_{GEN}=3\Omega$		12.4		ns
t_r	Turn-On Rise Time			8.2		ns
$t_{D(off)}$	Turn-Off DelayTime			25.6		ns
t_f	Turn-Off Fall Time			12		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-12\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		33		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-12\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		23		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.